



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Shuichi Kikuchi et al.
 Serial No. : 09/444,819
 Filed : November 22, 1999
 Title : SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

Art Unit : 2814
 Examiner : S. Rao

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Commissioner for Patents
 Washington, D.C. 20231

AMENDMENT

In response to the action mailed June 20, 2001, please amend the application as follows:

In the claims:

Please amend claim 1 as follows:

-- 1. (Amended) A semiconductor device comprising a source region, a channel region, a drain region, a gate electrode disposed above the channel region, and a drift region disposed adjacent to the channel region and extending to and below the drain region,
 wherein the drift region is formed shallowly at least below the gate electrode but formed deeply in a neighborhood of the drain region.--

Please add claim 19.

-- 19. (New) A semiconductor device according to claim 2, wherein the second conductive type drift region is formed to be adjacent to the first conductive type body region. --

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I hereby certify under 37 CFR §1.8(a) that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage on the date indicated below and is addressed to the Commissioner for Patents, Washington, D.C. 20231.

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